

Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers
- Controlled rectifiers

$I_{F(AV)}$ **5630 A**
 V_{RRM} **200~1000 V**
 I_{FSM} **58 kA**
 I^2t **16820 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT	
				Min	Type	Max		
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Double side cooled,	T _C =55°C	190			6600	A
			T _C =85°C				5630	
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} = V _{RRM} +100V	190	200		1000	V	
I _{RRM}	Repetitive peak current	V _{RM} = V _{RRM}	190			100	mA	
I _{FSM}	Surge forward current	10ms half sine wave	190			58	kA	
I ² t	I ² T for fusing coordination	V _R =0.6V _{RRM}				16820	A ² s*10 ³	
V _{FO}	Threshold voltage		190			0.63	V	
r _F	Forward slop resistance					0.058	mΩ	
V _{FM}	Peak on-state voltage	I _{FM} =5000A, F=32kN	190			1.02	V	
Q _{rr}	Recovery charge	F _M =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V	190		4500		μC	
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 32kN				0.013	°C /W	
R _{th(c-h)}	Thermal resistance case to heat sink					0.0035		
F _m	Mounting force			27		34	kN	
T _{stg}	Stored temperature			-40		190	°C	
W _t	Weight				850		g	
Outline	ZT60cT65							

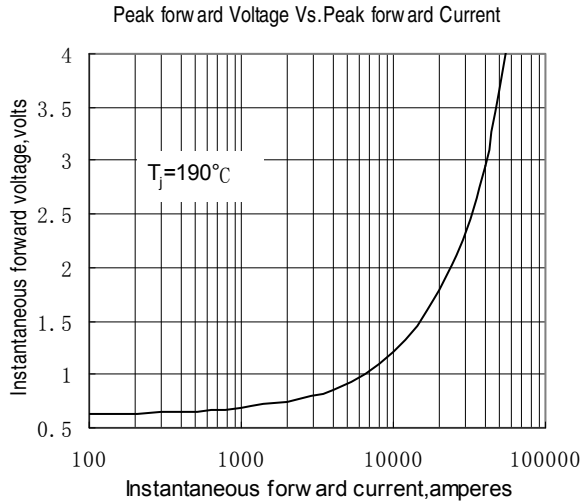


Fig.1

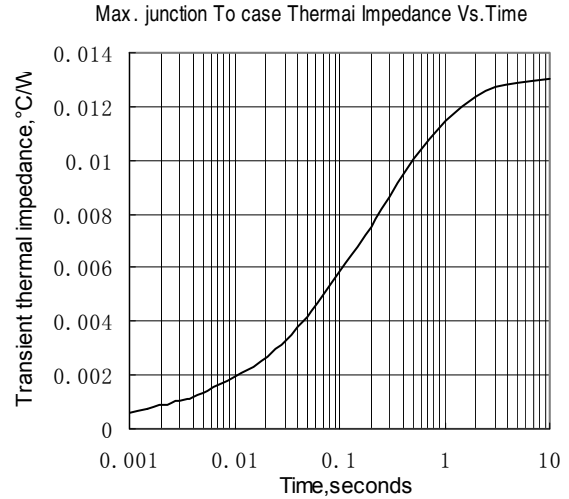


Fig.2

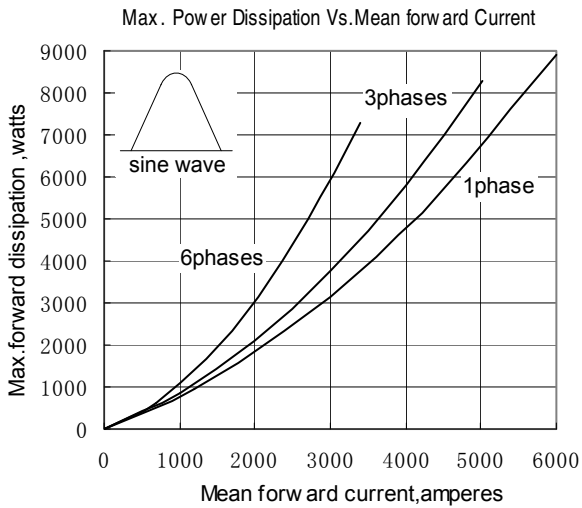


Fig.3

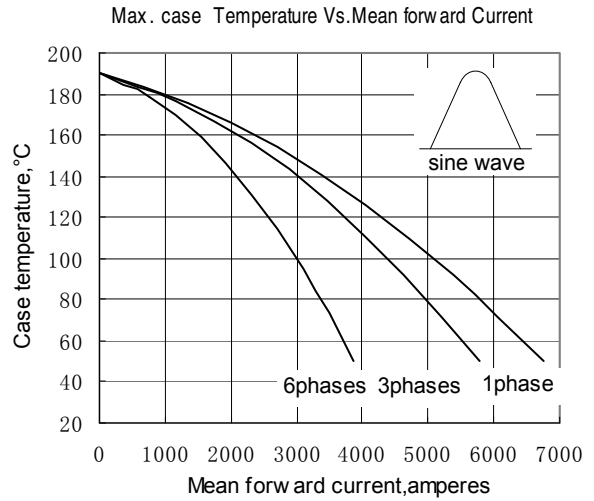


Fig.4

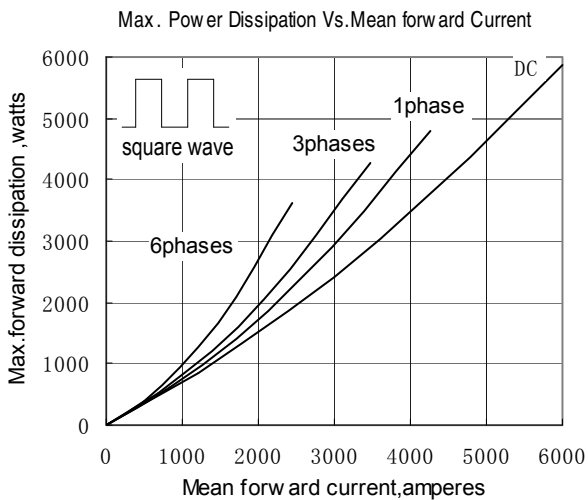


Fig.5

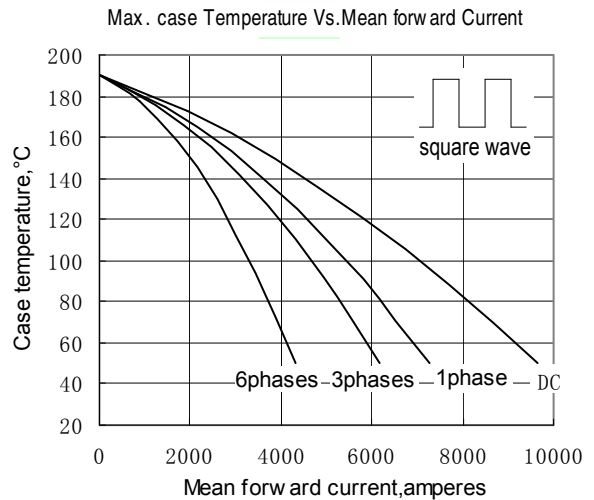


Fig.6

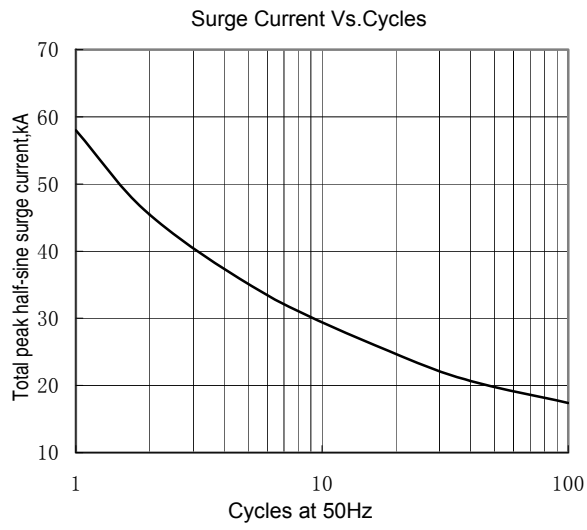


Fig.7

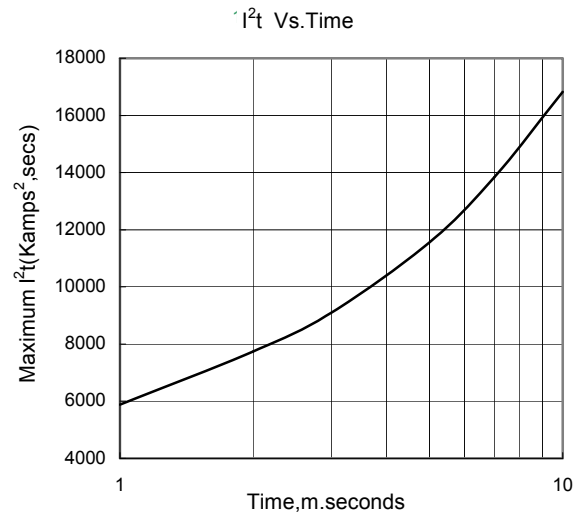


Fig.8

Outline:

